

## ABSTRACT

An object of the present invention is to provide an optimum ceramic substrate being excellent in temperature rising property and breakdown voltage and Young's modulus at a high temperature  
5 as a substrate for producing/examining a semiconductor, and in the ceramic substrate of the present invention having a conductor on a surface or inside thereof, the ceramic substrate has a leakage quantity of  $10^{-7}$  Pa · m<sup>3</sup> / sec (He) or less by measurement with a helium leakage detector.